

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-9. (Canceled)

10. (Original) A method for manufacturing a semiconductor device comprising the steps of:

processing a first laser beam with a wavelength of visible light or a shorter wavelength than visible light into a long beam at a surface of a semiconductor film or a vicinity thereof; and

crystallizing the semiconductor film by irradiating a second laser beam of a fundamental wave and the long beam at the same time to a region of the surface while moving the surface relatively with respect to the long beam in a direction.

11. (Original) A method for manufacturing a semiconductor device comprising the steps of:

processing a first laser beam with a wavelength of visible light or a shorter wavelength than visible light into a long beam at a surface of a semiconductor film or a vicinity thereof; and

activating an impurity region formed in the semiconductor film by irradiating a second laser beam of a fundamental wave and the long beam at the same time to a region of the surface while moving the surface relatively with respect to the long beam in a direction.

12. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor layer over a glass substrate;

forming an insulating layer for covering a top surface and side surface of the semiconductor layer;

forming a conductive layer over the semiconductor layer with the insulating layer therebetween;

processing a first laser beam with a wavelength of visible light or a shorter wavelength than visible light into a long beam at ~~[[a]]~~ an irradiated surface or a vicinity thereof; and

heating the conductive layer selectively to perform heat treatment of the semiconductor layer and the insulating layer by irradiating a second laser beam of a fundamental wave and the long beam at the same time to a region of the irradiated surface while moving the irradiated surface relatively in a direction with respect to the long beam.

13. (Original) A method for manufacturing a semiconductor device according to claim 10, wherein each of the first and second oscillators has continuous wave gas laser, solid laser, or metal laser.

14. (Original) A method for manufacturing a semiconductor device according to claim 10, wherein each of the first and second oscillators has Ar laser, Kr laser, CO₂ laser, YAG laser, YVO₄ laser, YLF laser, YAlO₃ laser, ruby laser, alexandrite laser, Ti:sapphire laser, helium-cadmium laser, copper vapor laser, or gold vapor laser.

15. (Original) A method for manufacturing a semiconductor device according to claim 11, wherein each of the first and second oscillators has continuous wave gas laser, solid laser, or metal laser.

16. (Original) A method for manufacturing a semiconductor device according to claim 11, wherein each of the first and second oscillators has Ar laser, Kr laser, CO₂ laser, YAG laser, YVO₄ laser, YLF laser, YAlO₃ laser, ruby laser, alexandrite laser, Ti:sapphire laser, helium-cadmium laser, copper vapor laser, or gold vapor laser.

17. (Original) A method for manufacturing a semiconductor device according to claim 12, wherein each of the first and second oscillators has continuous wave gas laser, solid laser, or metal laser.

18. (Original) A method for manufacturing a semiconductor device according to claim 12, wherein each of the first and second oscillators has Ar laser, Kr laser, CO₂ laser, YAG laser, YVO₄ laser, YLF laser, YAlO₃ laser, ruby laser, alexandrite laser, Ti:sapphire laser, helium-cadmium laser, copper vapor laser, or gold vapor laser.

19. (Canceled)

20. (Original) A method for manufacturing a semiconductor device comprising the steps of:

processing a first laser beam with a wavelength of visible light or a shorter wavelength than visible light into a long beam at a surface of a semiconductor film or a vicinity thereof; and

crystallizing the semiconductor film by irradiating a second laser beam of a fundamental wave and the long beam to a region of the surface while moving the surface relatively with respect to the long beam in a direction,

wherein the long beam is overlapped with the second laser beam at the region.

21. (Original) A method for manufacturing a semiconductor device comprising the steps of:

processing a first laser beam with a wavelength of visible light or a shorter wavelength than visible light into a long beam at a surface of a semiconductor film or a vicinity thereof; and

activating an impurity region formed in the semiconductor film by irradiating a second laser beam of a fundamental wave and the long beam at the same time to a region of the surface while moving the surface relatively with respect to the long beam in a direction,

wherein the long beam is overlapped with the second laser beam at the region.

22.-23. (Canceled)

24. (Original) A method for manufacturing a semiconductor device according to claim 20, wherein each of the first and second oscillators has continuous wave gas laser, solid laser, or metal laser.

25. (Original) A method for manufacturing a semiconductor device according to claim 20, wherein each of the first and second oscillators has Ar laser, Kr laser, CO₂ laser, YAG laser, YVO₄ laser, YLF laser, YAlO₃ laser, ruby laser, alexandrite laser, Ti:sapphire laser, helium-cadmium laser, copper vapor laser, or gold vapor laser.

26. (Original) A method for manufacturing a semiconductor device according to claim 21, wherein each of the first and second oscillators has continuous wave gas laser, solid laser, or metal laser.

27. (Original) A method for manufacturing a semiconductor device according to claim 21, wherein each of the first and second oscillators has Ar laser, Kr laser, CO₂ laser, YAG laser, YVO₄ laser, YLF laser, YAlO₃ laser, ruby laser, alexandrite laser, Ti:sapphire laser, helium-cadmium laser, copper vapor laser, or gold vapor laser.